

Technical Data Data Sheet N1250, Rev. A **Green Products** 

# 20SQ045L SCHOTTKY BARRIER RECTIFIER

## **Applications:**

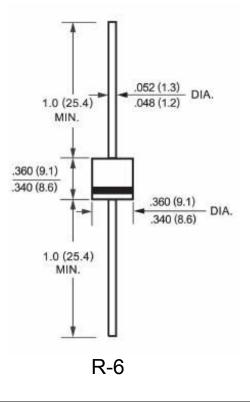
- DC-DC converters
- AC adapter
- High frequency rectification circuit
- Bypass diodes
- Photovoltaic Solar cell Protection Schottky Rectifier

## Features:

- Super-high speed & low noise switching
- Low voltage drop
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

## Mechanical Dimensions: In Inches/ mm





Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 (86) 25-87123907 •
 FAX (86) 25-87123900 • World Wide Web Site - http://www.sangdest.com.cn • E-Mail Address - sales@ sangdest.com.cn •



#### Technical Data Data Sheet N1250, Rev. A

**Green Products** 

#### Marking Diagram:



Where XXXXX is YYWWL

20	= Forward Current (20A)
S	= Package Type
Q	= Device Type
045	= Reverse Voltage (45V)
L	= Low VF
SSG	= SSG
YY	= Year
WW	= Week
L	= Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

#### **Ordering Information:**

Device	Package	Shipping
20SQ045L	R-6 (Pb-Free)	500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification.

#### **Maximum Rating:**

Characteristics	Symbol	Conditions	Value	Unit
Repetitive Peak Reverse Voltage	Vrrm	-	45	V
Max. average forward current	I <sub>F(AV)</sub>	R- load, Ta=25℃	20	Α
Surge(Non-repetitive) Forward Current	I <sub>FSM</sub>	8.3ms single half sine-wave	350	А

Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 
 (86) 25-87123907 
 FAX (86) 25-87123900 
 World Wide Web Site - http://www.sangdest.com.cn 
 E-Mail Address - sales@ sangdest.com.cn 



Technical Data Data Sheet N1250, Rev. A **Green Products** 

### Electrical Characteristics (Ta=25°C Unless otherwise specified)

Characteristics	Symbol	Conditions		Max.	Unit
Peak Forward Voltage	Vfm	Ігм=20.0А,Та=25℃		0.50	V
Peak Forward Voltage	Vfm	Ігм=20.0А,Та=125℃		0.45	V
Peak Reverse Current	IRRM1	VRM=VRRM	Ta=25℃	1.0	mA
	IRRM2	VRM-VRRM	Ta=125℃	200	ША
Max. Junction Capacitance (per leg)	CT	@V <sub>R</sub> = 5V, T <sub>C</sub> = 25 °C f <sub>SIG</sub> = 1MHz		1300	pF
Thermal Resistance(Typical)	R θJ-c	Between junction and case		3.0	°C/W
	R θJ-L	Between junction and lead		2.0	

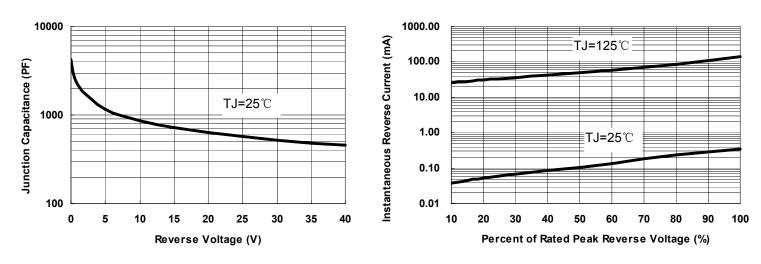
## **Thermal-Mechanical Specifications:**

Characteristics	Symbol	Condition	Specification	Units	
Junction Temperature	perature $T_J$ At reduced reverse $V_R \leq 80\% V_{RRM}$		-55 to +125	°C	
		At reduced reverse voltage: $V_R \leqslant 50\% V_{RRM}$	-55 to +180		
		In DC forward mode	-55 to +200		
Storage Temperature	T <sub>stg</sub>	-	-55 to +125	°C	
Approximate Weight	wt	-	2.24	g	
Case Style	R-6				

Weiqi Street, Airport Development Zone, Jiangning District, Nanjing, China 211113 (86) 25-87123907
 FAX (86) 25-87123900
 World Wide Web Site - http://www.sangdest.com.cn
 E-Mail Address - sales@ sangdest.com.cn



Technical Data Data Sheet N1250, Rev. A **Green Products** 





#### Fig.2-Typical Reverse Characteristics

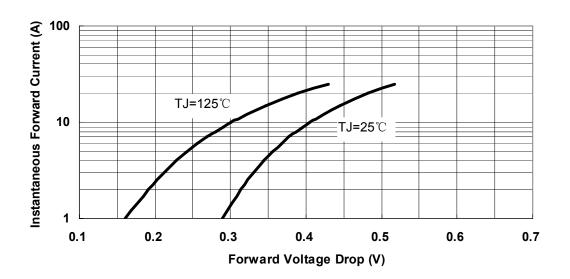


Fig.3-Typical Instantaneous Forward Voltage Characteristics



#### Technical Data Data Sheet N1250, Rev. A

#### **Green Products**

#### DISCLAIMER:

1- The information given herein, including the specifications and dimensions, is subject to change without prior notice to improve product characteristics. Before ordering, purchasers are advised to contact the SMC - Sangdest Microelectronics (Nanjing) Co., Ltd sales department for the latest version of the datasheet(s).

2- In cases where extremely high reliability is required (such as use in nuclear power control, aerospace and aviation, traffic equipment, medical equipment, and safety equipment), safety should be ensured by using semiconductor devices that feature assured safety or by means of users' fail-safe precautions or other arrangement.

3- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any damages that may result from an accident or any other cause during operation of the user's units according to the datasheet(s). SMC - Sangdest Microelectronics (Nanjing) Co., Ltd assumes no responsibility for any intellectual property claims or any other problems that may result from applications of information, products or circuits described in the datasheets.

. 4- In no event shall SMC - Sangdest Microelectronics (Nanjing) Co., Ltd be liable for any failure in a semiconductor device or any secondary damage resulting from use at a value exceeding the absolute maximum rating.

5- No license is granted by the datasheet(s) under any patents or other rights of any third party or SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.

6- The datasheet(s) may not be reproduced or duplicated, in any form, in whole or part, without the expressed written permission of SMC - Sangdest Microelectronics (Nanjing) Co., Ltd.

7- The products (technologies) described in the datasheet(s) are not to be provided to any party whose purpose in their application will hinder maintenance of international peace and safety nor are they to be applied to that purpose by their direct purchasers or any third party. When exporting these products (technologies), the necessary procedures are to be taken in accordance with related laws and regulations.